**Organization and Committees**

**Organizing Committee**
David Harame, IBM, USA  
Hiroshi Iwai, Tokyo Inst. Of Tech., Japan  
Junichi Murota, Tohoku Univ., Japan  
Derek Houghton, Aixtron, USA

**HBT Committee**
John Cressler, Chair (Georgia Tech., USA)  
A. Chantre (ST Microelectronics, France)  
J. Osten (Univ. Hannover, Germany)  
D. Knoll (IHP, Germany)  
K. Washio (Hitachi, Japan)  
G. Freeman (IBM, USA)  
G. Niu (Auburn Univ., USA)  
D. Enicks (ATMEL, USA)  
G.M. Olezek (Univ. Colorado, USA)  
M. Ostling (KTH, Sweden)

**FET Committee**
Ken Rim, Chair (IBM, USA)  
N. Sugiyama (MIRAI-ASET/Toshiba, Japan)  
J. Hoyt (MIT, USA)  
T. Skotniki (ST, France)  
S. Deleonibus (LETI, France)  
T.J. King (UC Berkeley)  
S. Banerjee (Univ. of Texas at Austin, USA)  
C. De Meyer (IMEC, Belgium)

**Optoelectronics Committee**
Lili Vescan, Chair (Forschungszentrum-Juelich, Austria)  
K Wada (MIT, USA)  
G. Masini (Univ. Roma Tre, Italy)  
S.P. Pogossian (CNRS, France)  
N. Usami (Tohoku U., Japan)  
G. Capellini (Luxtera, USA)  
H. Presting (DaimlerChrysler, Germany)  
D.-X. Xu (National Research Council, Canada)  
A. Vonsovici (Argessus Photonics, UK)

**Emerging Applications Committee**
Tsu-Jae King, Chair (Univ. Calif. at Berkeley, USA)  
Sherif Sedky (American Univ. in Cairo, Egypt)  
Hirobumi Watanabe (Ricoh Company, Ltd., Japan)

**Epitaxy and Processing Committee**
Bernd Tillack, Chair (IHP, Germany)  
D. Houghton (Aixtron, Canada)  
M.R. Caymax (IMEC, Belgium)  
J. Murota (Tohoku Univ., Japan)  
C.W. Liu (National Taiwan Univ., Taiwan)  
H Ruecker (IHP, Germany)  
A. Samoilov (Applied Materials Corp., USA)  
J Sakai (Anleva, Japan)  
Jianqing Wen (ASM, USA)  
Y. Kunii (Hitachi Kokusai Electric, Japan)

**Device Physics and Novel Structures Committee**
Derek Houghton, Chair (Aixtron, USA)  
M. Fischetti (IBM, USA)  
S. Banerjee (Univ. of Texas at Austin, USA)  
J. Ramm (Unaxis, Liechtenstein)  
F. Lu (Fudan U. Shanhui China)  
S. Takagi (MiraI-Aset/Thoshiba)  
S Zaima (Nagoya Univ., Japan)

**Invited Speakers (Partial List)**
Judy Hoyt, MIT, "Strained Si/SiGe FETs"  
Shinichi Takagi, U. of Tokyo / ASET, "Strained Si on SGOI Devices"  
Tahir Ghanji, Intel, "Uniaxial-strained Si FETs for high performance"  
Gianlorenzo Masini, NOOEL Nonlinear Optics and optoelectronics Lab, "Si-based near-infrared detection and emission"  
Dan-Xia Xu, IMS, Optoelectronic Devices, "Photonic components based on Si and SiGe"  
Bahram Jalali, UCLA, "Light Generation, Amplification, Wavelength Conversion, and 3-D Fabrication: Advanced Topics in Silicon Photonics"  
Dr. Wilhelm Frey, Bosch, "Industrial Application of Poly-SiGe as Functional MEMS Material"  
M.Thiel, Bosch, "RF/Analog Applications for low voltage SiGe BiCMOS Processes"  
A.Chantre, ST, "0.13um SiGe:C HBT Technology"  
B.Heinemann, IHP, "Complementary SiGe BiCMOS"  
M.Wurzer, Infineon, SiGe HBT Circuit Applications
**Symposium Topics**

The first International SiGe: Materials, Processing, and Devices Symposium is part of the 2004 ECS conference to be held in Honolulu Hawaii from October 3-6. This meeting will provide a forum for reviewing and discussing all materials and device related aspects of SiGe. There are 6 areas of interest for the Symposium described below:

1. **Epitaxy and Processing**
   All aspects of surface preparation and growth of epitaxial, SiGe(C) layers. All aspects of processing including diffusion, oxidation, strain, thermal mixing, and defects.

2. **Device Physics and Novel Structures**
   Small structure formation, Self-assembled island nucleation, Quantum Wires and Dots, and Calculation of electronic properties including band structures.

3. **Optoelectronics**
   Light emitting diodes (LEDs) and photodetectors, on passive components and monolithic optoelectronic integrated circuits (OEICs).

4. **Heterojunction Bipolar Transistors**
   Device physics, process technology, modeling issues, and circuit applications of SiGe

5. **FET Technology**
   SSCMOS, SiGe FET structures, SiGe HEMTs, SiGe MODFETs, SiGe FET structures on SOI, RTD, Low voltage – low power devices

6. **Emerging Applications**
   Electro-mechanical properties of SiGe layers, MEMs, TFTs, amorphous SiGe layer applications

---

**Instructions for Authors**

**Symposium Details**

For the latest symposium details please see the website at: [www.ecs2004sige.org](http://www.ecs2004sige.org)

**Conference Fees and Registration**

The symposium is part of the Fall 2004 Electrochemical Society Conference so registration and Fees are paid directly to the ECS. Please see [www.electrochem.org](http://www.electrochem.org) for all conference details.

**Paper Submission**

Authors should send an e-file version (.pdf or .doc) of a one page summary consisting of text and figures using the ECS extended abstract format to the symposium manager Jan Jopke ccs@mn.rr.com, no later than March 8, 2004. Author instructions and a template for the summary are available at the symposium web-site: [http://www.ecs2004sige.org](http://www.ecs2004sige.org).

---

**How to find the Symposium**

**SiGe Symposium/ECS Conference Site:** Hilton Hawaiian Village in Honolulu Hawaii.

[www.electrochem.org/meetings/future/206/meeting.htm](http://www.electrochem.org/meetings/future/206/meeting.htm)


Phone: +808 - 949 - 4321

---

Please send manuscripts to the symposium manager Jan Jopke at ccs@mn.rr.com

**Symposium proceedings**

The symposium proceedings will be available at the symposium. All authors will need to submit a full-length manuscript for the symposium proceedings which is due April 23rd. Detailed instructions and templates for the preparation of the full-length manuscript can be found at the symposium web-site: [http://www.ecs2004sige.org](http://www.ecs2004sige.org).